Nuclear Instruments and Methods in Physics Research B37/38 (1989) 979–994
North-Holland, Amsterdam

AUTHOR INDEX

Adachi, Y., see Kimura, T. B37/38 (1989) 321
Agawa, Y., see Takagi, K. B37/38 (1989) 169
Agawa, Y., see Nishihashi, T. B37/38 (1989) 205
Agawa, Y., see Mihara, Y. B37/38 (1989) 609
Aihara, R., H. Sawaragi, B. Thompson and M.H. Shearer, Development of focused ion beam systems B37/38 (1989) 212
Akasaka, Y., Current status of ion implantation for VLSI applications B37/38 (1989) 9
Akiba, M., see Tanaka, S. B37/38 (1989) 128
Alberda, H., see Polman, A. B37/38 (1989) 935
Alton, G.D., The sputter generation of negative ion beams B37/38 (1989) 45
Amemiya, K., K. Tokiguchi, H. Koike, T. Seki and N. Sakudo, New microwave ion source for high energy ion implanter B37/38 (1989) 87
Amemiya, K., see Tokiguchi, K. B37/38 (1989) 253
Anderle, M., see Solmi, S. B37/38 (1989) 394
Anzlowar, M., see White, A.E. B37/38 (1989) 923
Aoki, S., see Horiuchi, M. B37/38 (1989) 285
Aono, M., M. Katayama, E. Nomura, T. Chassé, D. Choi and M. Kato, Recent developments in low-energy ion scattering spectroscopy (ISS) for surface structural analysis B37/38 (1989) 264
Aoyama, T., see Koshida, N. B37/38 (1989) 708
Aoyama, Y., see Ishikawa, J. B37/38 (1989) 151
Appleton, B.R., see Zuhr, R.A. B37/38 (1989) 16
Araki, M., see Inoue, T. B37/38 (1989) 111
Araki, M., see Tanaka, S. B37/38 (1989) 128
Arimatsu, K., I. Hashimoto, S. Ooishi, S. Tanaka, T. Sato and T. Gejyo, Development of large scale ion beam milling machines B37/38 (1989) 833
Arimatsu, K., see Hashimoto, I. B37/38 (1989) 838
Arnold, G.W., W.K. Schubert, C.H. Seager, M.J. Carr, G.C. Nelson and B.L. Doyle, Physical and electrical properties of oxides grown on carbon-implanted silicon B37/38 (1989) 429
Asari, M., see Hirakimoto, A. B37/38 (1989) 248
Attema, I., see Polman, A. B37/38 (1989) 935

Baba, T., see Takano, I. B37/38 (1989) 688
Bacal, M., Volume production of hydrogen negative ions B37/38 (1989) 28
Baldwin, K.W., see White, A.E. B37/38 (1989) 923
Bannenberg, J., see Thomae, R.W. B37/38 (1989) 235
Bannenberg, J.G. and F.W. Saris, High energy implantation: present and future facilities B37/38 (1989) 398
Bannenberg, J.G., see Urbanus, W.H. B37/38 (1989) 508
Bannenberg, J.G., see Polman, A. B37/38 (1989) 935
Bao, X.-M., Q. Gu and X.-F. Huang, Behavior of hydrogen during laser crystallization and RTA of a-Si:H SOI B37/38 (1989) 391
Barth, M., see Wolf, G.K. B37/38 (1989) 682
Barthel, A., J. Lorenz and H. Ryssel, Two-dimensional simulation of ion implantation profiles using a personal computer B37/38 (1989) 312
Batstone, J.L., see Poate, J.M. B37/38 (1989) 955
Baumvol, I.J.R., see Vasconcellos, M.A.Z. B37/38 (1989) 653
Becker, B.L., see Rathmell, R.D. B37/38 (1989) 497
Benveniste, V., H.E. Friedman, M.E. Mack and F. Sinclair, In situ monitoring of wafer charging during ion implantation B37/38 (1989) 568
Berrian, D.W., R.E. Kaim, J.W. Vanderpot and J.F.M. Westendorp, The ASM-220 medium current implanter B37/38 (1989) 500
Berrian, D.W., R.E. Kaim and J.W. Vanderpot, In situ uniformity control, dose monitoring and correction B37/38 (1989) 518
Bhattacharyya, A., see Current, M.I. B37/38 (1989) 555
Biersack, J.P., see Xia, W. B37/38 (1989) 408
Bivas, A., see Powell, R.A. B37/38 (1989) 339
Boisseau, P., A. Dart, A.S. Denholm, H.F. Glavish, B. Libby and G. Simcox, Production high-energy ion implanters with milliampere beam capabilities B37/38 (1989) 591

0168-583X/89/$03.50 © Elsevier Science Publishers B.V.
(North-Holland Physics Publishing Division)

Borden, P., see Weisenberger, W. ... B37/38 (1989) 644
Borges da Costa, J.A.T., see Vasconcellos, M.A.Z. ... B37/38 (1989) 653
Braun, M., H. Khosroupour, E. Johansson and S. Hogmark, Formation and characterization of carbon layers deposited during ion bombardment of silicon ... B37/38 (1989) 434
Breeden, T., see Simonton, R. ... B37/38 (1989) 543
Brown, I.G., Advances in metal ion sources ... B37/38 (1989) 68
Brown, W.L., Ion beam induced chemical changes in molecular solids ... B37/38 (1989) 270
Buchanan, R.A., see Williams, J.M. ... B37/38 (1989) 676

Calcagno, L., see Coffa, S. ... B37/38 (1989) 296
Calcagno, L., see Marletta, G. ... B37/38 (1989) 712
Calleri, G., see Coffa, S. ... B37/38 (1989) 296
Campisano, S.U., see Coffa, S. ... B37/38 (1989) 296
Canteri, R., see Solmi, S. ... B37/38 (1989) 394
Carr, M.J., see Arnold, G.W. ... B37/38 (1989) 429
Cembali, F., see Solmi, S. ... B37/38 (1989) 394
Černý, R., see Musil, J. ... B37/38 (1989) 897
Chassé, T., see Aono, M. ... B37/38 (1989) 264
Chater, R.J., see Hemment, P.L.F. ... B37/38 (1989) 766
Chen Lizhi, see Xing Kunshan ... B37/38 (1989) 741
Cheng Shichang, Fu Dejun, Zhang Hui and Pan Xianzheng, A reaction sputtering type rf ion source for solid elements ... B37/38 (1989) 136
Chereckdjian, S., see Weisenberger, W. ... B37/38 (1989) 644
Cheung, N.W., see Mutikainen, R.H. ... B37/38 (1989) 716
Cheung, N.W., C.L. Liang, B.K. Liew, R.H. Mutikainen and H. Wong, Buried dopant and defect layers for device structures with high-energy ion implantation ... B37/38 (1989) 941
Cheung, N.W., see Wong, H. ... B37/38 (1989) 970
Choi, D., see Aono, M. ... B37/38 (1989) 264
Christensen, K.N., see Hemment, P.L.F. ... B37/38 (1989) 766
Chu, W.K., M.Z. Numan, J.Z. Zhang, G.S. Sandhu and A.E. Michel, Transient diffusion of boron implanted in Si along random and channeling directions ... B37/38 (1989) 365
Ciavola, G., see La Ferla, A. ... B37/38 (1989) 951
Clark, G.J., see Marwick, A.D. ... B37/38 (1989) 910
Coffa, S., L. Calcagno, G. Calleri, G. Ferla and S.U. Campisano, Gold implantation in silicon: diffusion studies and device applications ... B37/38 (1989) 296
Cornelius, W.D., Sources of polarized ions and atoms ... B37/38 (1989) 56
Cornely, R., see Sosnowski, M. ... B37/38 (1989) 870
Current, M.I., A. Bhattacharyya and M. Khidr, Control of surface charging during high current ion implantation ... B37/38 (1989) 555
Current, M.I., see Felch, S.B. ... B37/38 (1989) 563

Dai, Y., see Kobayashi, K. ... B37/38 (1989) 704
Daniel, R.E., see Norton, G.A. ... B37/38 (1989) 403
Dart, A., see Boisseau, P. ... B37/38 (1989) 591
Davis, J.R., see Hemment, P.L.F. ... B37/38 (1989) 766
De Haas, E., see Polman, A. ... B37/38 (1989) 935
De Potter, M., see Langouche, G. ... B37/38 (1989) 438
Decker, J.H., see Rathmell, R.D. ... B37/38 (1989) 497
Deitinghoff, H., see Thomae, R.W. ... B37/38 (1989) 235
Delforge, A., see Liebert, R.B. ... B37/38 (1989) 464
Delforge, A., see Liebert, R.B. ... B37/38 (1989) 533
Delforge, A., see Hertel, R. ... B37/38 (1989) 580
Denholm, A.S., see Boisseau, P. ... B37/38 (1989) 591
Derks, J., see Polman, A. ... B37/38 (1989) 935
Dézsi, I., see Langouche, G. ... B37/38 (1989) 438
Doherty, B.J. and D.J. McCarron, Ion beam induced wafer charging ... B37/38 (1989) 559
Doi, M., see Suezawa, Y. ... B37/38 (1989) 735
Doorn, S., see Polman, A. ... B37/38 (1989) 935
Doyle, B.L., see Arnold, G.W. ... B37/38 (1989) 429
Dykstra, J.P., see Samayan, S.E. ... B37/38 (1989) 90
Dykstra, J.P., see Fleming, J.L. ... B37/38 (1989) 601
Dynes, R.C., see White, A.E. ... B37/38 (1989) 923

Egner, B., see Meyer, O. B37/38 (1989) 917
Ehinger, K., see Kakoschke, R. B37/38 (1989) 823
Elliman, R.G., see Thornton, R.P. B37/38 (1989) 387
Enloe, D.T., Ion implanter automation for manufacturability: comparisons and recommendations B37/38 (1989) 521
Ensinger, W., see Wolf, G.K. B37/38 (1989) 682
Evans, E., see Mears, E. B37/38 (1989) 460
Evans, E., see Liebert, R.B. B37/38 (1989) 464
Evans, E., see Satoh, S. B37/38 (1989) 612

Fabbri, R., see Solmi, S. B37/38 (1989) 394
Fair, R.B., The role of transient damage annealing in shallow junction formation B37/38 (1989) 371
Fairbairn, K., Precision Implant 9200 – An implantation system for 200 mm wafers B37/38 (1989) 596
Fan Weidong, see Zhao Qihua B37/38 (1989) 336
Fan, X., see Pan, X. B37/38 (1989) 858
Fang Ziwei, see Lin Chenglu B37/38 (1989) 384
Felch, S.B., see Powell, R.A. B37/38 (1989) 339
Felch, S.B., L.A. Larson, M.I. Current and D.W. Lindsey, Analysis techniques of charging damage studied on three different high-current ion implanters B37/38 (1989) 563
Ferla, G., see Coffa, S. B37/38 (1989) 296
Ferla, G., see La Ferla, A. B37/38 (1989) 951
Fernandes, M., see Xia, W. B37/38 (1989) 408
Fischer, P., Scan compensation for Varian serial implanters B37/38 (1989) 525
Fleming, J.L., J.P. Dykstra, M.L. King, A.M. Ray and R.B. Simonton, NV-6208: a midcurrent ion implanter with constant beam angle of incidence B37/38 (1989) 601
Foti, G., see Marletta, G. B37/38 (1989) 712
Freytsis, A., see Hertel, R. B37/38 (1989) 580
Friedman, H.E., see Benveniste, V. B37/38 (1989) 568
Frisa, L.E., see Samayan, S.E. B37/38 (1989) 90
Fu Dejun, see Cheng Shichang B37/38 (1989) 136
Fujihana, T., see Kobayashi, K. B37/38 (1989) 704
Fujii, K., see Takai, M. B37/38 (1989) 244
Fujii, K., see Kiuchi, M. B37/38 (1989) 701
Fujimoto, F., see Kiuchi, M. B37/38 (1989) 701
Fujisawa, H., see Nagai, N. B37/38 (1989) 572
Fujita, H., see Hirakimoto, A. B37/38 (1989) 248
Fujita, K., see Takaoka, G.H. B37/38 (1989) 882
Fukui, R., K. Takagi, T. Tsugueda, H. Tsuboi, R. Kikuchi, E. Yabe and K. Takayama, Long life plasma filament type ion source B37/38 (1989) 140
Fukui, R., see Takagi, K. B37/38 (1989) 169
Fukui, R., see Kogure, S. B37/38 (1989) 201
Fukui, R., see Mihara, Y. B37/38 (1989) 609
Fukui, S., see Ogawa, S. B37/38 (1989) 163
Fukumaru, F., see Inami, H. B37/38 (1989) 198
Fukumasa, O., S. Saeki and S. Shiratake, Enhancement of H^- production in a multicusp source by proper selection of wall material B37/38 (1989) 176
Fukumoto, S., see Mori, Y. B37/38 (1989) 63

Garno, J.P., see White, A.E. B37/38 (1989) 923
Geary, C., see Harada, M. B37/38 (1989) 528
Geerk, J., see Meyer, O. B37/38 (1989) 917
Gejyo, T., see Arimatsu, K. B37/38 (1989) 833
Gejyo, T., see Hashimoto, I. B37/38 (1989) 838
Gerber, R., see Meyer, O. B37/38 (1989) 917
Giles, A.D., see Wauk, M.T. B37/38 (1989) 442
Glavish, H.F., see Boisseau, P. B37/38 (1989) 591
Glawischnig, H. and R. Ploss, Paperless datalogger: concept and realization for an implanter B37/38 (1989) 588
Glawischnig, H. and G. Lang, Round-robin "ion-implanter and 4-point probes" B37/38 (1989) 624
Gondō, Y., see Suezawa, Y. B37/38 (1989) 735
Götz, G., see Machalett, F. B37/38 (1989) 180
Gspann, J., High-intensity ionized cluster beams of large metal clusters B37/38 (1989) 775
Gu, Q., see Bao, X.-M. B37/38 (1989) 391

Guerra, M.A., see Wittkower, A.B. ... B37/38 (1989) 512
Guzinski, M., see Sosnowski, M. ... B37/38 (1989) 870
Gyulai, J. and I. Krafcsik, Comparative status of pulsed ion implantation ... B37/38 (1989) 275

Hakamata, Y., T. Iga, K. Natsui and T. Sato, Bucket type ion source using a microwave plasma cathode ... B37/38 (1989) 143
Hanada, M., see Inoue, T. ... B37/38 (1989) 111
Hanawa, T., see Oura, K. ... B37/38 (1989) 975
Harada, M., C. Geary and R. Outcault, Automation features in the 160 XP high current implanter ... B37/38 (1989) 528
Harada, M., see Sunouchi, T. ... B37/38 (1989) 548
Haraichi, S., see Yamaguchi, H. ... B37/38 (1989) 891
Harano, Y., see Shiono, T. ... B37/38 (1989) 166
Harbeke, G., see Steigmeier, E.F. ... B37/38 (1989) 304
Hashimoto, I., see Arimatsu, K. ... B37/38 (1989) 833
Hashimoto, I., K. Arimatsu, Y. Ishikawa, S. Tanaka and T. Gejyo, Development of a high deposition rate machine by ion beam sputtering ... B37/38 (1989) 838
Häuser, J., see Thomae, R.W. ... B37/38 (1989) 235
Haynes, T.E., see Zuhr, R.A. ... B37/38 (1989) 16
Hemment, P.L.F., see Reeson, K.J. ... B37/38 (1989) 290
Hemment, P.L.F., see Steigmeier, E.F. ... B37/38 (1989) 304
Hemment, P.L.F., K.J. Reeson, A.K. Robinson, J.A. Kilner, R.J. Chater, C.D. Marsh, K.N. Christensen and J.R. Davis, Nonplanar and noncontinuous buried layers of SiO_2 in silicon formed by ion beam synthesis ... B37/38 (1989) 766
Herbots, N., see Zuhr, R.A. ... B37/38 (1989) 16
Hertel, R., see Liebert, R.B. ... B37/38 (1989) 533
Hertel, R., A. Freytsis, E. Mears and A. Delforge, A vacuum exchange end station for a new batch process ion implantation system ... B37/38 (1989) 580
Hewett, C.A., see Xia, W. ... B37/38 (1989) 408
Higuchi, T., M. Sato and T. Tamai, A wafer charge-up-reducing system of a high-current ion implanter ... B37/38 (1989) 605
Higuchi, T., see Okada, K. ... B37/38 (1989) 640
Hioki, T., see Itoh, A. ... B37/38 (1989) 692
Hiraki, A., see Sekoguchi, M. ... B37/38 (1989) 728
Hiraki, A., H. Kawarada, K.-S. Mar, Y. Yokota, J. Wei and J.-I. Suzuki, Deposition of wide-area diamond films in magneto-microwave plasma ... B37/38 (1989) 799
Hirakimoto, A., H. Nakanishi, H. Fujita, I. Konishi, S. Nagamachi, H. Nakahara and M. Asari, An RFQ accelerator system for MeV ion implantation ... B37/38 (1989) 248
Hirao, Y., see Tokiguchi, K. ... B37/38 (1989) 253
Hirofuji, Y., see Ohnishi, T. ... B37/38 (1989) 850
Hirofuji, Y., see Yoshida, Y. ... B37/38 (1989) 866
Hodul, D. and S. Metha, The use of semiconductor processes for the design and characterization of a rapid thermal processor ... B37/38 (1989) 818
Hogmark, S., see Braun, M. ... B37/38 (1989) 434
Hong, Q.Z., see Hung, L.S. ... B37/38 (1989) 414
Horiuchi, M., M. Tamura and S. Aoki, Gate-edge effects on SPE regrowth from As^+-implanted Si ... B37/38 (1989) 285
Horiuchi, M., see Tamura, M. ... B37/38 (1989) 329
Hoshino, A., see Takagi, K. ... B37/38 (1989) 169
Huang, X.-F., see Bao, X.-M. ... B37/38 (1989) 391
Hughes, W.E., see Kaufman, H.R. ... B37/38 (1989) 98
Hung, L.S., Q.Z. Hong and J.W. Mayer, Thermal and ion induced silicide formation ... B37/38 (1989) 414
Hyouzho, M., see Tamura, S. ... B37/38 (1989) 862

Iga, T., see Hakamata, Y. ... B37/38 (1989) 143
Ikeda, T., see Yoshida, Y. ... B37/38 (1989) 866
Ikegami, K., see Mori, Y. ... B37/38 (1989) 63
Ikehata, T., H. Mase and T. Tanabe, Extraction of intense plasma beams of metal ions from a magnetized coaxial diode operated in vacuum-arc mode ... B37/38 (1989) 107
Ikehata, T., see Mase, H. ... B37/38 (1989) 120
Imada, K., see Yamanishi, K. ... B37/38 (1989) 930
Ina, T., Y. Minowa, N. Koshirakawa and K. Yamanishi, Development of an ionized cluster beam system for large-area deposition ... B37/38 (1989) 779
Ina, T., see Ito, H. ... B37/38 (1989) 814
Inami, H., F. Fukumaru, Y. Inouchi, D. Sato, K. Tanaka and K. Matsunaga, Development of high current metal ion beam source ... B37/38 (1989) 198
Inouchi, Y., see Inami, H. ... B37/38 (1989) 198

Inoue, K., see Takai, M. B37/38 (1989) 260
Inoue, M., see Ishikawa, K. B37/38 (1989) 317
Inoue, T., M. Araki, M. Hanada, T. Kurashima, S. Matsuda, Y. Matsuda, Y. Ohara, Y. Okumura, S. Tanaka and K. Watanabe, Multi-ampere negative hydrogen ion source for fusion application B37/38 (1989) 111
Ishibashi, K., see Takai, M. B37/38 (1989) 260
Ishii, S., H. Oyama and H. Odagiri, Fundamental study of ECR multicharged ion sources B37/38 (1989) 147
Ishikawa, J., A heavy negative ion sputter source: production mechanism of negative ions and their applications B37/38 (1989) 38
Ishikawa, J., H. Tsuji, T. Kashiwagi, Y. Aoyama and T. Takagi, Direct deposition of focused ion beams with an impregnated-electrode-type liquid metal ion source B37/38 (1989) 151
Ishikawa, J., H. Tsuji, T. Kashiwagi and T. Takagi, Intense metal ion beam formation by an impregnated-electrode-type liquid metal ion source B37/38 (1989) 155
Ishikawa, J., see Tsuji, H. B37/38 (1989) 159
Ishikawa, J., see Tsuji, H. B37/38 (1989) 231
Ishikawa, J., see Takaoka, G.H. B37/38 (1989) 783
Ishikawa, J., see Takaoka, G.H. B37/38 (1989) 882
Ishikawa, K., M. Yoshida and M. Inoue, Depth profiles of secondary defects of As^+ and BF_2^+ implanted silicon measured by a thermal wave technique B37/38 (1989) 317
Ishikawa, Y., see Hashimoto, I. B37/38 (1989) 838
Ishitani, T., see Umemura, K. B37/38 (1989) 208
Ishitani, T., see Kawanami, Y. B37/38 (1989) 240
Isobe, S., see Takano, I. B37/38 (1989) 688
Isoya, A., see Nishihashi, T. B37/38 (1989) 205
Isoya, A., see Mihara, Y. B37/38 (1989) 609
Ito, H., Y. Minowa and T. Ina, High-speed low-temperature film preparation by an ionized cluster beam, assisted by an ionized gas beam B37/38 (1989) 814
Itoh, A., T. Hioki and J. Kawamoto, Tribological properties of ion implanted SiC ceramics B37/38 (1989) 692
Iwaki, M., Formation of metal surface layers with high performance by ion implantation B37/38 (1989) 661
Iwaki, M., see Kobayashi, K. B37/38 (1989) 704
Iwamoto, K., see Okada, T. B37/38 (1989) 720
Iwamoto, K., see Okada, T. B37/38 (1989) 724
Iwasaki, H., see Ohnishi, T. B37/38 (1989) 850
Iwasaki, H., see Yoshida, Y. B37/38 (1989) 866
Iwase, M., see Masaki, S. B37/38 (1989) 846
Izumi, K., Y. Omura and S. Nakashima, Modification of a 100-mA-class high-current oxygen implanter and its application to ultrathin film MOSFET/SIMOX B37/38 (1989) 299

Jacobson, D.C., see Poate, J.M. B37/38 (1989) 955
Janssen, K.T.F., see Westendorp, J.F.M. B37/38 (1989) 357
Jiang Binyao, see Yang Genqing B37/38 (1989) 424
Jiang Xinyuan, see Zhao Qihua B37/38 (1989) 336
Johansson, E., see Braun, M. B37/38 (1989) 434

Kadlec, S., see Musil, J. B37/38 (1989) 897
Kadono, K., see Kiuchi, M. B37/38 (1989) 701
Kaim, R.E., see Westendorp, J.F.M. B37/38 (1989) 357
Kaim, R.E., see Berrian, D.W. B37/38 (1989) 500
Kaim, R.E., see Berrian, D.W. B37/38 (1989) 518
Kaim, R.E., see Pollock, J.D. B37/38 (1989) 576
Kakoschke, R., Temperature problems with rapid thermal processing for VLSI applications B37/38 (1989) 753
Kakoschke, R. and K. Ehinger, Shallow junction formation by boron implantation with energies between 2 and 5 keV and rapid thermal annealing B37/38 (1989) 823
Kamenitsa, D., see Simonton, R. B37/38 (1989) 344
Kamenitsa, D.E., see Simonton, R. B37/38 (1989) 616
Kanazawa, S., M. Kogoma, S. Okazaki and T. Moriwaki, Glow plasma treatment at atmospheric pressure for surface modification and film deposition B37/38 (1989) 842
Kashiwagi, T., see Ishikawa, J. B37/38 (1989) 151
Kashiwagi, T., see Ishikawa, J. B37/38 (1989) 155
Katagawa, T., see Takagi, K. B37/38 (1989) 169
Katagawa, T., see Nishihashi, T. B37/38 (1989) 205
Katagawa, T., see Mihara, Y. B37/38 (1989) 609
Katagiri, K., see Okada, T. B37/38 (1989) 720

Katagiri, K., see Okada, T. ... B37/38 (1989) 724
Katayama, M., see Aono, M. ... B37/38 (1989) 264
Katayama, S., see Tamura, S. ... B37/38 (1989) 862
Kato, M., see Aono, M. ... B37/38 (1989) 264
Kato, T., Focused ion beam technologies for lithographic applications ... B37/38 (1989) 218
Kaufman, H.R., W.E. Hughes, R.S. Robinson and G.R. Thompson, Thirty-eight-centimeter ion source ... B37/38 (1989) 98
Kawagoe, Y., see Yamanishi, K. ... B37/38 (1989) 930
Kawai, T., see Matsuda, K. ... B37/38 (1989) 456
Kawai, T., see Nagai, N. ... B37/38 (1989) 572
Kawakami, H., see Sasaki, M. ... B37/38 (1989) 469
Kawamoto, J., see Itoh, A. ... B37/38 (1989) 692
Kawamoto, Y., see Tamura, M. ... B37/38 (1989) 329
Kawanami, Y., see Umemura, K. ... B37/38 (1989) 208
Kawanami, Y., T. Ishitani and K. Umemura, Focused ion beam system with a four stage $E \times B$ mass filter ... B37/38 (1989) 240
Kawarada, H., see Hiraki, A. ... B37/38 (1989) 799
Kawase, Y. and K. Okano, The oxidation technique for efficient ionization of lanthanides by a helium-jet loaded on-line isotope separator ... B37/38 (1989) 116
Kawata, Y., see Takai, M. ... B37/38 (1989) 260
Keenan, W.A., see Yarling, C.B. ... B37/38 (1989) 828
Keller, R., B.R. Nielsen and B. Torp, Metal beam production using a high current ion source ... B37/38 (1989) 74
Kersten, H., see Polman, A. ... B37/38 (1989) 935
Khidr, M., see Current, M.I. ... B37/38 (1989) 555
Khosroupour, H., see Braun, M. ... B37/38 (1989) 434
Kido, Y., Growth mechanism and magnetic properties of AlMn metastable phase formed by ion beam mixing ... B37/38 (1989) 696
Kikuchi, R., see Fukui, R. ... B37/38 (1989) 140
Kikuchi, R., see Takagi, K. ... B37/38 (1989) 169
Kikuchi, R., see Nishihashi, T. ... B37/38 (1989) 205
Kikuchi, R., see Mihara, Y. ... B37/38 (1989) 609
Kikuchi, S., see McKenna, C.M. ... B37/38 (1989) 492
Kilner, J.A., see Hemment, P.L.F. ... B37/38 (1989) 766
Kimura, S., see Tabata, O. ... B37/38 (1989) 906
Kimura, T., see Yamada, T. ... B37/38 (1989) 94
Kimura, T., M. Kuwata, Luo Ji-Kui, S. Yugo and Y. Adachi, Deep levels in indium phosphide implanted with argon and phosphorus ... B37/38 (1989) 321
King, M., see Simonton, R. ... B37/38 (1989) 616
King, M.L., see Samayan, S.E. ... B37/38 (1989) 90
King, M.L., see Fleming, J.L. ... B37/38 (1989) 601
Kinomura, A., see Takai, M. ... B37/38 (1989) 244
Kirillov, D., see Powell, R.A. ... B37/38 (1989) 339
Kishimoto, M., see Tabata, O. ... B37/38 (1989) 906
Kitchen, R.L., see Rathmell, R.D. ... B37/38 (1989) 497
Kiuchi, M., see Takai, M. ... B37/38 (1989) 244
Kiuchi, M., K. Fujii, H. Miyamura, K. Kadono, M. Satou and F. Fujimoto, Film formation of dititanium nitride by the dynamic mixing method ... B37/38 (1989) 701
Klein, H., see Thomae, R.W. ... B37/38 (1989) 235
Klein, H., see Urbanus, W.H. ... B37/38 (1989) 508
Kluge, A., see Öchsner, R. ... B37/38 (1989) 504
Kluge, A., H. Ryssel and R. Schork, A flexible target chamber for a Varian 350 DF implanter ... B37/38 (1989) 584
Knodle, W., see Weisenberger, W. ... B37/38 (1989) 644
Kobashi, A., see Okada, T. ... B37/38 (1989) 724
Kobayashi, K., S. Namba, T. Fujihana, Y. Dai and M. Iwaki, Effect of incident angles of N implantation on recrystallization of AlN_x thin films ... B37/38 (1989) 704
Kogoma, M., see Kanazawa, S. ... B37/38 (1989) 842
Kogure, S., A. Tonegawa, K. Takayama, R. Fukui and K. Takagi, Hollow cathode ion source developed for metal ions ... B37/38 (1989) 201
Kohno, I., Production of fast-switching power thyristors by proton irradiation ... B37/38 (1989) 739
Koike, H., see Amemiya, K. ... B37/38 (1989) 87
Koike, H., see Sakudo, N. ... B37/38 (1989) 184
Koike, H., see Tokiguchi, K. ... B37/38 (1989) 253
Kojima, T., see Oura, K. ... B37/38 (1989) 975
Konishi, I., see Hirakimoto, A. ... B37/38 (1989) 248

Koshida, N., Y. Suzuki and T. Aoyama, Low energy ion implantation studies of polyacetylene films B37/38 (1989) 708
Koshikawa, T., see Mihara, Y. B37/38 (1989) 609
Koshirakawa, N., see Ina, T. B37/38 (1989) 779
Koudijs, R., A new 500 kV ion accelerator for ion-implantation and analyzing purposes B37/38 (1989) 649
Koyanagi, T., T. Watanabe, K. Nakamura, K. Yamano and K. Matsubara, Magneto-optical properties of $Cd_{1-x}Mn_xTe$ multilayered structures prepared by ionized-cluster beams B37/38 (1989) 878
Krafcsik, I., see Gyulai, J. B37/38 (1989) 275
Krop, H., see Polman, A. B37/38 (1989) 935
Kumasaki, H., see Tamura, Y. B37/38 (1989) 620
Kumazaki, H., see Sasaki, M. B37/38 (1989) 469
Kunori, M., see Okada, T. B37/38 (1989) 720
Kunori, M., see Okada, T. B37/38 (1989) 724
Kurashima, T., see Inoue, T. B37/38 (1989) 111
Kuratomi, Y., see Nunogaki, M. B37/38 (1989) 325
Kuwano, H., see Mizushima, I. B37/38 (1989) 807
Kuwata, M., see Kimura, T. B37/38 (1989) 321
Kužel Jr, R., see Musil, J. B37/38 (1989) 897

La Ferla, A., E. Rimini, G. Ciavola and G. Ferla, Very high energy implants of boron into silicon B37/38 (1989) 951
Lang, G., see Glawischnig, H. B37/38 (1989) 624
Langouche, G., M. De Potter, I. Dézsi, M.F. Wu and A. Vantomme, Mössbauer spectroscopy study of the thermal annealing behavior of very low and very high dose Co-implanted Si B37/38 (1989) 438
Larson, L.A., see Felch, S.B. B37/38 (1989) 563
Larson, L.A., A comparison of wafer resistivity probing tools B37/38 (1989) 628
Lau, S.S., see Xia, W. B37/38 (1989) 408
Lee, I.-S., see Williams, J.M. B37/38 (1989) 676
Lee, J.K., see McKenna, C.M. B37/38 (1989) 492
Leipe, P., see Thomae, R.W. B37/38 (1989) 235
Leung, K.N., Development of high current and high brightness negative hydrogen ion sources B37/38 (1989) 33
Levi, A.F.J., see White, A.E. B37/38 (1989) 923
Levin, J.P., see Wagner, A. B37/38 (1989) 224
Liang, C.L., see Cheung, N.W. B37/38 (1989) 941
Libby, B., see Boisseau, P. B37/38 (1989) 591
Licciardello, A., see Marletta, G. B37/38 (1989) 712
Liebert, R., see Mears, E. B37/38 (1989) 460
Liebert, R.B., S. Satoh, A. Delforge and E. Evans, Dose control system for the Extrion 1000 ion implantation system B37/38 (1989) 464
Liebert, R.B., A. Delforge, R. Hertel, H. Lulsdorf, E. Mears and S. Satoh, The Extrion 1000: a new high current ion implantation system for automated fabrication environments and intelligent process control B37/38 (1989) 533
Liebert, R.B., see Satoh, S. B37/38 (1989) 612
Liew, B.K., see Cheung, N.W. B37/38 (1989) 941
Lin Chenglu, see Zhao Qihua B37/38 (1989) 336
Lin Chenglu, Fang Ziwei, Zhou Wei, Ni Rushan and Zou Shichang, A study of molecular arsenic ion implantation in silicon B37/38 (1989) 384
Lin Chenglu, see Xing Kunshan B37/38 (1989) 741
Lin, H.-Y. and C.H. Ting, Improvement of CMOS latch-up immunity using a high energy implanted buried layer B37/38 (1989) 960
Lindsey, D.W., see Felch, S.B. B37/38 (1989) 563
Linker, G., see Meyer, O. B37/38 (1989) 917
Liu, B.X., see Shang, C.H. B37/38 (1989) 420
Liu Xianghuai, see Zhao Qihua B37/38 (1989) 336
Liu Xianghuai, see Yang Genqing B37/38 (1989) 424
Liu Xianghuai, see Zou Shichang B37/38 (1989) 672
Loger, R.L., see Norton, G.A. B37/38 (1989) 403
Lorenz, J., see Barthel, A. B37/38 (1989) 312
Lotti, R., see Solmi, S. B37/38 (1989) 394
Luck, T.R., see Rathmell, R.D. B37/38 (1989) 497
Lulsdorf, H., see Liebert, R.B. B37/38 (1989) 533
Lundquist, P., Dosimetry system characteristics which effect wafer uniformity B37/38 (1989) 538
Luo Ji-Kui, see Kimura, T. B37/38 (1989) 321

Machalett, F., R. Mühle, I. Stiebritz and G. Götz, Mass spectra of Au–Ge alloy liquid metal ion sources B37/38 (1989) 180
Mack, M.E., Charging and charge neutralization in ion implantation B37/38 (1989) 472
Mack, M.E., see Benveniste, V. B37/38 (1989) 568
Maeda, T., see Tamura, Y. B37/38 (1989) 620
Maekawa, T., see Tsuji, H. B37/38 (1989) 231
Mahony, C.M.O., see Proudfoot, G. B37/38 (1989) 103
Mar, K.-S., see Hiraki, A. B37/38 (1989) 799
Marletta, G., A. Licciardello, L. Calcagno and G. Foti, Reflection electron energy loss spectroscopy of keV bombarded polystyrene at high ion fluences B37/38 (1989) 712
Marsh, C.D., see Hemment, P.L.F. B37/38 (1989) 766
Marwick, A.D. and G.J. Clark, Ion implantation in high-T_c superconductors B37/38 (1989) 910
Masaki, S., M. Iwase and H. Morisaki, Optimization of the ion-to-atom arrival rate for ion beam assisted Ge deposition B37/38 (1989) 846
Mase, H., see Ikehata, T. B37/38 (1989) 107
Mase, H., T. Tanabe and T. Ikehata, Superdense hollow cathode glow discharge and its application to ion sources B37/38 (1989) 120
Matsubara, K., see Koyanagi, T. B37/38 (1989) 878
Matsuda, K., T. Kawai and M. Naito, High current implantation equipment B37/38 (1989) 456
Matsuda, S., see Inoue, T. B37/38 (1989) 111
Matsuda, S., see Tanaka, S. B37/38 (1989) 128
Matsuda, Y., see Inoue, T. B37/38 (1989) 111
Matsuda, Y., see Tanaka, S. B37/38 (1989) 128
Matsugatani, K., see Takaoka, G.H. B37/38 (1989) 783
Matsunaga, K., see Inami, H. B37/38 (1989) 198
Matsuo, T., see Takai, M. B37/38 (1989) 244
Matsuo, T., see Takai, M. B37/38 (1989) 260
Mayer, J.W., see Hung, L.S. B37/38 (1989) 414
McCarron, D.J., see Doherty, B.J. B37/38 (1989) 559
McKenna, C.M., New development in ion implantation and RTP equipment for high productivity B37/38 (1989) 448
McKenna, C.M., B.O. Pedersen, J.K. Lee, R.F. Outcault and S. Kikuchi, Wafer charging control in the 160 XP high current implanter B37/38 (1989) 492
McRay, R.F., see Pollock, J.D. B37/38 (1989) 576
Mears, E., E. Evans, K. Pierce and R. Liebert, New method of solid state wafer cooling in the Extrion 1000 high current ion implantation system B37/38 (1989) 460
Mears, E., see Liebert, R.B. B37/38 (1989) 533
Mears, E., see Hertel, R. B37/38 (1989) 580
Metha, S., see Hodul, D. B37/38 (1989) 818
Meyer, O., B. Egner, J. Geerk, R. Gerber, G. Linker, F. Weschenfelder, X.X. Xi and G.C. Xiong, Epitaxial growth of $YBa_2Cu_3O_7$ thin films and the influence of ion irradiation on the transport properties B37/38 (1989) 917
Michel, A.E., see Chu, W.K. B37/38 (1989) 365
Michel, A.E., Anomalous transient diffusion of ion implanted dopants: a phenomenological model B37/38 (1989) 379
Mihara, Y., see Nishihashi, T. B37/38 (1989) 205
Mihara, Y., T. Uchiyama, Y. Agawa, R. Fukui, T. Katagawa, O. Tsukakoshi, P. Rostek, H. Tsuboi, K. Takagi, H. Yamakawa, R. Kikuchi, A. Isoya and T. Koshikawa, The development of a 400 keV ion accelerator for surface study and atomic collision experiments B37/38 (1989) 609
Mikami, H., see Uchitomi, N. B37/38 (1989) 810
Milgate, R.W., see Pollock, J.D. B37/38 (1989) 576
Minowa, Y., see Ina, T. B37/38 (1989) 779
Minowa, Y., see Ito, H. B37/38 (1989) 814
Miyamura, H., see Kiuchi, M. B37/38 (1989) 701
Miyazaki, K., see Nunogaki, M. B37/38 (1989) 325
Mizushima, I., K. Ohori and H. Kuwano, Solid-phase recrystallization of Si-ion-implanted polycrystalline silicon films B37/38 (1989) 807
Moore, R.A., see Samayan, S.E. B37/38 (1989) 90
Mori, Y., A. Takagi, K. Ikegami, A. Ueno and S. Fukumoto, New results from the KEK ion source development projects B37/38 (1989) 63
Morisaki, H., see Masaki, S. B37/38 (1989) 846
Moriwaki, T., see Kanazawa, S. B37/38 (1989) 842
Mühle, R., see Machalett, F. B37/38 (1989) 180
Murai, Y., see Oomori, T. B37/38 (1989) 124

Musil, J., V. Poulek, S. Kadlec, J. Vyskočil, V. Valvoda, R. Černý, R. Kužel,Jr, Effect of ion bombardment on the structure of sputtered Ti–N films B37/38 (1989) 897
Mutikainen, R.H., H. Wong and N.W. Cheung, High energy implantation masking with polyimide B37/38 (1989) 716
Mutikainen, R.H., see Cheung, N.W. B37/38 (1989) 941

Nagai, N., T. Kawai, M. Naito, Y. Nishigami, H. Fujisawa and K. Nishikawa, Wafer chargeup study on the PR-80 high current ion implantation machine B37/38 (1989) 572
Nagamachi, S., see Hirakimoto, A. B37/38 (1989) 248
Naito, M., see Matsuda, K. B37/38 (1989) 456
Naito, M., see Nagai, N. B37/38 (1989) 572
Nakahara, H., see Hirakimoto, A. B37/38 (1989) 248
Nakajima, M., see Tamba, M. B37/38 (1989) 173
Nakamura, K. and T. Nozaki, Substitutional site control of Si in GaAs by stoichiometry change with Ga ion implantation B37/38 (1989) 308
Nakamura, K., see Koyanagi, T. B37/38 (1989) 878
Nakanishi, H., see Hirakimoto, A. B37/38 (1989) 248
Nakashima, S., see Izumi, K. B37/38 (1989) 299
Namba, S., see Takai, M. B37/38 (1989) 244
Namba, S., see Takai, M. B37/38 (1989) 260
Namba, S., see Kobayashi, K. B37/38 (1989) 704
Natsuaki, N., see Ohyu, K. B37/38 (1989) 749
Natsui, K., see Hakamata, Y. B37/38 (1989) 143
Nelson, G.C., see Arnold, G.W. B37/38 (1989) 429
Ni Rushan, see Lin Chenglu B37/38 (1989) 384
Nielsen, B.R., see Keller, R. B37/38 (1989) 74
Nihei, T., see Noguchi, T. B37/38 (1989) 632
Nihei, T., see Sunako, K. B37/38 (1989) 636
Nishigami, Y., see Nagai, N. B37/38 (1989) 572
Nishihashi, T., H. Tsuboi, Y. Mihara, Y. Agawa, T. Uchiyama, N. Ueda, T. Katagawa, K. Takagi, H. Yamakawa, R. Kikuchi and A. Isoya, Negative ion source for the tandem accelerator B37/38 (1989) 205
Nishijima, S., see Okada, T. B37/38 (1989) 720
Nishijima, S., see Okada, T. B37/38 (1989) 724
Nishikawa, K., see Nagai, N. B37/38 (1989) 572
Nishiura, T., see Okada, T. B37/38 (1989) 724
Nogami, M., see Tamura, Y. B37/38 (1989) 620
Noggle, T.S., see Zuhr, R.A. B37/38 (1989) 16
Noguchi, T., T. Tanikawa, K. Yamauchi, T. Nihei, H. Watanabe, K. Sunako and K. Takayama, A concept for isotope separation in a sheet plasma by using ion cyclotron resonance heating B37/38 (1989) 632
Noguchi, T., see Sunako, K. B37/38 (1989) 636
Nomura, A., see Tabata, O. B37/38 (1989) 906
Nomura, E., see Aono, M. B37/38 (1989) 264
Norton, G.A., R.E. Daniel, R.L. Loger and J.B. Schroeder, Present developments of research MeV Pelletron ion implantation systems B37/38 (1989) 403
Nosaka, T., see Ogawa, S. B37/38 (1989) 163
Nozaki, T., see Nakamura, K. B37/38 (1989) 308
Numan, M.Z., see Chu, W.K. B37/38 (1989) 365
Nunogaki, M., M. Uchida, Y. Kuratomi and K. Miyazaki, Surface roughness and sputtering yield of heavily ion implanted surfaces B37/38 (1989) 325

Öchsner, R., A. Kluge and H. Ryssel, A versatile ion implanter for material modification B37/38 (1989) 504
O'Connor, J.P., N. Tokoro, J. Smith and M. Sieradzki, Performance characteristics of the Genus Inc. IX-1500 high energy ion implantation system B37/38 (1989) 478
Odagiri, H., see Ishii, S. B37/38 (1989) 147
Odlum, G.B., see Westendorp, J.F.M. B37/38 (1989) 357
Ogawa, H., see Yamada, T. B37/38 (1989) 94
Ogawa, S., A. Okamoto, K. Takiguchi, M. Yoshitake, T. Nosaka, S. Fukui and T. Ueno, Development of a low energy ion source with multicapillary anode B37/38 (1989) 163
Ogawa, S., see Suzuki, Y. B37/38 (1989) 854
Ohara, Y., see Inoue, T. B37/38 (1989) 111
Ohara, Y., see Tanaka, S. B37/38 (1989) 128
Ohmi, T. and T. Shibata, Very-low-temperature thin-film formation technology by a low-kinetic-energy particle process B37/38 (1989) 794

Ohnishi, T., Y. Yoshida, Y. Hirofuji and H. Iwasaki, Ta_2O_5 film formation by double ion beam method B37/38 (1989) 850
Ohnishi, T., see Yoshida, Y. B37/38 (1989) 866
Ohori, K., see Mizushima, I. B37/38 (1989) 807
Ohyu, K., T Suzuki, T. Yamanaka and N. Natsuaki, Feasibility of high-energy boron implantation for p-type retrograde well formation B37/38 (1989) 749
Okada, K., T. Higuchi, T. Shiraishi, M. Sato and T. Tamai, The NV-10SD high-current ion implantation system B37/38 (1989) 640
Okada, T., S. Nishijima, K. Takahata, K. Katagiri, M. Kunori and K. Iwamoto, Electrical properties of polyimide films implanted with nitrogen and argon B37/38 (1989) 720
Okada, T., T. Nishiura, K. Katagiri, S. Nishijima, K. Iwamoto, M. Kunori and A. Kobashi, Friction and wear of nitrogen implanted aluminum alloy based FRM B37/38 (1989) 724
Okamoto, A., see Ogawa, S. B37/38 (1989) 163
Okano, K., see Kawase, Y. B37/38 (1989) 116
Okazaki, S., see Kanazawa, S. B37/38 (1989) 842
Okumura, Y., see Inoue, T. B37/38 (1989) 111
Okumura, Y., see Tanaka, S. B37/38 (1989) 128
Omura, Y., see Izumi, K. B37/38 (1989) 299
Ono, K., see Oomori, T. B37/38 (1989) 124
Ooishi, S., see Arimatsu, K. B37/38 (1989) 833
Oomori, T., K. Ono and Y. Murai, Generation of pure gallium ion beams by field ionization of laser-excited Rydberg atoms B37/38 (1989) 124
Oura, K., T. Kojima, F. Shoji and T. Hanawa, Monte Carlo simulation of channeling effects in high energy (MeV) phosphorus ion implantation into crystalline silicon targets B37/38 (1989) 975
Outcault, R., see Harada, M. B37/38 (1989) 528
Outcault, R.F., see McKenna, C.M. B37/38 (1989) 492
Oyama, H., see Ishii, S. B37/38 (1989) 147

Pan, F., see Pan, X. B37/38 (1989) 858
Pan, X., X. Fan, F. Pan, M. Zhang and Z. Zhu, New equipment for preparation of films by assisted deposition . B37/38 (1989) 858
Pan Xianzheng, see Cheng Shichang B37/38 (1989) 136
Parker, M.A., see Sigmon, T.W. B37/38 (1989) 280
Pedersen, B.O., see McKenna, C.M. B37/38 (1989) 492
Pennycook, S.J., see Zuhr, R.A. B37/38 (1989) 16
Perrin, R., see Proudfoot, G. B37/38 (1989) 103
Pierce, K., see Mears, E. B37/38 (1989) 460
Ploss, R., see Glawischnig, H. B37/38 (1989) 588
Poate, J.M., F. Priolo, D.C. Jacobson, J.L. Batstone and M.O. Thompson, Epitaxial recrystallization and diffusion phenomena in amorphous silicon produced by MeV ion beams B37/38 (1989) 955
Poker, D.B., see Xia, W. B37/38 (1989) 408
Pollock, J.D., R.W. Milgate, R.F. McRay and R.E. Kaim, Features of the ASM-220 end station B37/38 (1989) 576
Polman, A., A.M. Vredenberg, W.H. Urbanus, P.J. Van Deenen, H. Alberda, H. Krop, I. Attema, E. De Haas, H. Kersten, S. Doorn, J. Derks, J. Ter Beek, S. Roorda, R. Schreutelkamp, J.G. Bannenberg and F.W. Saris, An MeV facility for materials research B37/38 (1989) 935
Poulek, V., see Musil, J. B37/38 (1989) 897
Powell, R.A., S.B. Felch, D. Kirillov and A. Bivas, A photoluminescence method of mapping dose uniformity in GaAs substrates B37/38 (1989) 339
Priolo, F., see Poate, J.M. B37/38 (1989) 955
Proudfoot, G., C.M.O. Mahony and R. Perrin, Development and use of a large area ultralow energy reactive ion beam B37/38 (1989) 103

Raatz, J.E., see Rathmell, R.D. B37/38 (1989) 497
Rathmell, R.D., J.E. Raatz, B.L. Becker, R.L. Kitchen, T.R. Luck and J.H. Decker, The VP 7-200 batch-processing wafer handler B37/38 (1989) 497
Ray, A.M., see Fleming, J.L. B37/38 (1989) 601
Reeson, K.J., K.G. Stephens and P.L.F. Hemment, Optimisation of SIMOX structures formed by ion beam synthesis B37/38 (1989) 290
Reeson, K.J., see Steigmeier, E.F. B37/38 (1989) 304
Reeson, K.J., see Hemment, P.L.F. B37/38 (1989) 766
Rimini, E., see La Ferla, A. B37/38 (1989) 951
Robinson, A.K., see Steigmeier, E.F. B37/38 (1989) 304
Robinson, A.K., see Hemment, P.L.F. B37/38 (1989) 766
Robinson, R.S., see Kaufman, H.R. B37/38 (1989) 98

Roorda, S., see Polman, A. ... B37/38 (1989) 935
Rose, P.H., Advanced ion beam equipment used for semiconductor production ... B37/38 (1989) 22
Rostek, P., see Mihara, Y. ... B37/38 (1989) 609
Ryssel, H., see Barthel, A. ... B37/38 (1989) 312
Ryssel, H., see Öchsner, R. ... B37/38 (1989) 504
Ryssel, H., see Kluge, A. ... B37/38 (1989) 584

Saeki, S., see Fukumasa, O. ... B37/38 (1989) 176
Sakai, K., see Sakudo, N. ... B37/38 (1989) 184
Sakamoto, Y., see Tamba, M. ... B37/38 (1989) 173
Sakase, T., see Satoh, S. ... B37/38 (1989) 612
Sakudo, N., see Amemiya, K. ... B37/38 (1989) 87
Sakudo, N., H. Koike, K. Tokiguchi, T. Seki and K. Sakai, Emittances of a microwave ion source for implantation ... B37/38 (1989) 184
Sakudo, N., see Tokiguchi, K. ... B37/38 (1989) 253
Sampayan, S.E., M.L. King, L.E. Frisa, R.A. Moore and J.P. Dykstra, Enhanced ionization Freeman ion source B37/38 (1989) 90
Sandhu, G.S., see Chu, W.K. ... B37/38 (1989) 365
Saris, F.W., see Westendorp, J.F.M. ... B37/38 (1989) 357
Saris, F.W., see Bannenberg, J.G. ... B37/38 (1989) 398
Saris, F.W., see Polman, A. ... B37/38 (1989) 935
Sasaki, M., M. Tanaka, H. Kawakami and H. Kumazaki, Beam scanning system for large tilt angle ion implantation ... B37/38 (1989) 469
Sasaki, M., see Sunouchi, T. ... B37/38 (1989) 548
Sasao, M., see Wada, M. ... B37/38 (1989) 132
Sato, D., see Inami, H. ... B37/38 (1989) 198
Sato, K., see Yamanishi, K. ... B37/38 (1989) 930
Sato, M., see Higuchi, T. ... B37/38 (1989) 605
Sato, M., see Okada, K. ... B37/38 (1989) 640
Sato, S., see Sunouchi, T. ... B37/38 (1989) 548
Sato, T., see Hakamata, Y. ... B37/38 (1989) 143
Sato, T., see Arimatsu, K. ... B37/38 (1989) 833
Sato, Y., see Yamada, T. ... B37/38 (1989) 94
Satoh, S., see Liebert, R.B. ... B37/38 (1989) 464
Satoh, S., see Liebert, R.B. ... B37/38 (1989) 533
Satoh, S., T. Sakase, E. Evans and R.B. Liebert, Ion beam system for the new high current ion implantation system Extrion-1000 ... B37/38 (1989) 612
Satou, M., see Takai, M. ... B37/38 (1989) 244
Satou, M., see Kiuchi, M. ... B37/38 (1989) 701
Sawaragi, H., see Aihara, R. ... B37/38 (1989) 212
Schempp, A., see Thomae, R.W. ... B37/38 (1989) 235
Schempp, A., see Urbanus, W.H. ... B37/38 (1989) 508
Schneemeyer, L.F., see White, A.E. ... B37/38 (1989) 923
Schork, R., see Kluge, A. ... B37/38 (1989) 584
Schreiner, W.H., see Vasconcellos, M.A.Z. ... B37/38 (1989) 653
Schreutelkamp, R., see Westendorp, J.F.M. ... B37/38 (1989) 357
Schreutelkamp, R., see Polman, A. ... B37/38 (1989) 935
Schroeder, J.B., see Norton, G.A. ... B37/38 (1989) 403
Schubert, W.K., see Arnold, G.W. ... B37/38 (1989) 429
Seager, C.H., see Arnold, G.W. ... B37/38 (1989) 429
Sedgwick, T.O., Rapid thermal processing, an integral part of shallow junction formation ... B37/38 (1989) 760
Seki, T., see Amemiya, K. ... B37/38 (1989) 87
Seki, T., see Sakudo, N. ... B37/38 (1989) 184
Seki, T., see Tokiguchi, K. ... B37/38 (1989) 253
Sekoguchi, M., T. Taguchi and A. Hiraki, Effects of ion irradiation on the optical properties of ZnSe–ZnS strained-layer superlattices ... B37/38 (1989) 728
Serikawa, T. and S. Shirai, Studies of H_2^+ implantation into indium–tin oxide films ... B37/38 (1989) 732
Servidori, M., see Solmi, S. ... B37/38 (1989) 394
Shang, C.H. and B.X. Liu, Metastable phase and dendritic pattern formation in thin solid films by ion mixing ... B37/38 (1989) 420
Shearer, M.H., see Aihara, R. ... B37/38 (1989) 212
Shibata, T., see Ohmi, T. ... B37/38 (1989) 794
Shibuya, T., see Shiono, T. ... B37/38 (1989) 166

Shimase, A., see Yamaguchi, H. ... B37/38 (1989) 891
Shiono, T., T. Shibuya, Y. Harano, E. Yabe and K. Takayama, Ion source with plasma cathode for ion assisted deposition ... B37/38 (1989) 166
Shirai, S., see Serikawa, T. ... B37/38 (1989) 732
Shiraishi, T., see Okada, K. ... B37/38 (1989) 640
Shiratake, S., see Fukumasa, O. ... B37/38 (1989) 176
Shoji, F., see Oura, K. ... B37/38 (1989) 975
Short, K.T., see White, A.E. ... B37/38 (1989) 923
Sieradzki, M., see O'Connor, J.P. ... B37/38 (1989) 478
Sigmon, T.W. and M.A. Parker, Solid phase epitaxial processes in implant-amorphized semiconductors ... B37/38 (1989) 280
Simcox, G., see Boisseau, P. ... B37/38 (1989) 591
Simonton, R. and D. Kamenitsa, Channeling control in silicon ⟨111⟩ substrates by target orientation ... B37/38 (1989) 344
Simonton, R. and T. Breeden, Low dose implant performance monitoring of a medium current ion implanter ... B37/38 (1989) 543
Simonton, R., M. King and D.E. Kamenitsa, Higher charge state ion beam purity in the Eaton medium current implanter ... B37/38 (1989) 616
Simonton, R.B., see Zrudsky, D.R. ... B37/38 (1989) 361
Simonton, R.B., see Fleming, J.L. ... B37/38 (1989) 601
Sinclair, F., see Benveniste, V. ... B37/38 (1989) 568
Sioshansi, P., Surface modification of industrial components by ion implantation ... B37/38 (1989) 667
Smith, J., see O'Connor, J.P. ... B37/38 (1989) 478
Smith, T.C., Particle contamination in implanters ... B37/38 (1989) 486
Solmi, S., F. Cembali, R. Fabbri, R. Lotti, M. Servidori, M. Anderle and R. Canteri, Dependence of transient enhanced diffusion on defect depth position in ion implanted silicon ... B37/38 (1989) 394
Sosnowski, M., M. Guzinski and R. Cornely, Atomic nitrogen generation system for reactive deposition of thin films ... B37/38 (1989) 870
Sosnowski, M. and I. Yamada, Deposition of thin films of copper on silicon substrates at low temperature by the ICB method ... B37/38 (1989) 874
Steigmeier, E.F., G. Harbeke, K.J. Reeson, P.L.F. Hemment and A.K. Robinson, Nondestructive assessment of SIMOX substrates ... B37/38 (1989) 304
Stelmack, L.A., C.T. Thurman and G.R. Thompson, Review of ion-assisted deposition: research to production ... B37/38 (1989) 787
Stephens, K.G., see Reeson, K.J. ... B37/38 (1989) 290
Stiebritz, I., see Machalett, F. ... B37/38 (1989) 180
Suezawa, Y., Y. Gondō, M. Doi and S.Z. Sun, High dose implantation of bismuth ions into 3d transition metal films ... B37/38 (1989) 735
Sun, S.Z., see Suezawa, Y. ... B37/38 (1989) 735
Sunako, K., see Noguchi, T. ... B37/38 (1989) 632
Sunako, K., K. Yamauchi, T. Noguchi, T. Nihei, H. Watanabe, T. Tanikawa, K. Takayama and T. Tsugueda, Production, characteristics and some applications of sheet plasmas ... B37/38 (1989) 636
Sunouchi, T., M. Sasaki, S. Sato and M. Harada, New computer control system for the high current ion implanter PR-80 ... B37/38 (1989) 548
Suzuki, J.-I., see Hiraki, A. ... B37/38 (1989) 799
Suzuki, S., see Tabata, O. ... B37/38 (1989) 906
Suzuki, T., see Ohyu, K. ... B37/38 (1989) 749
Suzuki, Y., see Koshida, N. ... B37/38 (1989) 708
Suzuki, Y., M. Yoshitake, T. Yotsuya, K. Takiguchi and S. Ogawa, ZnO crystal orientation change by bias voltage application to substrate or target in ion beam sputtering ... B37/38 (1989) 854
Szajnowski, W.J., Nonintrusive position measurement of magnetically scanned ion beams ... B37/38 (1989) 552

Tabata, O., S. Kimura, M. Kishimoto, M. Takahashi, A. Nomura and S. Suzuki, Deceleration of ion beams for film deposition by an electrostatic field ... B37/38 (1989) 906
Tagami, T. and S. Tanaka, Influence of plasma parameters on ion transport directionality in a glow discharge sheath ... B37/38 (1989) 256
Taguchi, T., see Sekoguchi, M. ... B37/38 (1989) 728
Takagi, A., see Mori, Y. ... B37/38 (1989) 63
Takagi, K., see Fukui, R. ... B37/38 (1989) 140
Takagi, K., T. Tsugueda, R. Fukui, H. Tsuboi, T. Katagawa, H. Yamakawa, A. Hoshino, Y. Agawa, R. Kikuchi and K. Takayama, A high current sheet plasma ion source ... B37/38 (1989) 169
Takagi, K., see Kogure, S. ... B37/38 (1989) 201
Takagi, K., see Nishihashi, T. ... B37/38 (1989) 205
Takagi, K., see Mihara, Y. ... B37/38 (1989) 609
Takagi, T., A perspective of eV–MeV ion beams ... B37/38 (1989) 1

Takagi, T., see Ishikawa, J. ... B37/38 (1989) 151
Takagi, T., see Ishikawa, J. ... B37/38 (1989) 155
Takagi, T., see Tsuji, H. ... B37/38 (1989) 159
Takagi, T., see Tsuji, H. ... B37/38 (1989) 231
Takagi, T., see Takaoka, G.H. ... B37/38 (1989) 783
Takagi, T., see Takaoka, G.H. ... B37/38 (1989) 882
Takagi, T., see Usui, H. ... B37/38 (1989) 886
Takagi, T., see Yamamura, Y. ... B37/38 (1989) 902
Takahashi, M., see Tabata, O. ... B37/38 (1989) 906
Takahashi, T., see Yamaguchi, H. ... B37/38 (1989) 891
Takahata, K., see Okada, T. ... B37/38 (1989) 720
Takai, M., A. Kinomura, T. Matsuo, S. Namba, M. Satou, M. Kiuchi and K. Fujii, Influence of excitation current deviation of a quadrupole magnet on beam spot size for MeV microbeams ... B37/38 (1989) 244
Takai, M., T. Matsuo, S. Namba, K. Inoue, K. Ishibashi and Y. Kawata, Microbeamline design for medium to high energy helium ion beams ... B37/38 (1989) 260
Takano, I., S. Isobe, M. Takemoto and T. Baba, Effect of N_2^+ ion dose on the hardness and other properties of AlN thin films prepared by the dynamic mixing method ... B37/38 (1989) 688
Takaoka, G.H., K. Matsugatani, J. Ishikawa and T. Takagi, Silicon nitride and oxide film formation by the simultaneous use of a microwave ion source and an ICB system ... B37/38 (1989) 783
Takaoka, G.H., K. Fujita, J. Ishikawa and T. Takagi, Grain boundary diffusion control of Cu films prepared by the ICB technique ... B37/38 (1989) 882
Takayama, K., see Fukui, R. ... B37/38 (1989) 140
Takayama, K., see Shiono, T. ... B37/38 (1989) 166
Takayama, K., see Takagi, K. ... B37/38 (1989) 169
Takayama, K., see Kogure, S. ... B37/38 (1989) 201
Takayama, K., see Noguchi, T. ... B37/38 (1989) 632
Takayama, K., see Sunako, K. ... B37/38 (1989) 636
Takeda, A., see Wada, T. ... B37/38 (1989) 348
Takeda, A., see Wada, T. ... B37/38 (1989) 352
Takemoto, M., see Takano, I. ... B37/38 (1989) 688
Takiguchi, K., see Ogawa, S. ... B37/38 (1989) 163
Takiguchi, K., see Suzuki, Y. ... B37/38 (1989) 854
Tamai, T., see Higuchi, T. ... B37/38 (1989) 605
Tamai, T., see Okada, K. ... B37/38 (1989) 640
Tamba, M., K. Yamaguchi, S. Tanaka, M. Yamawaki, M. Nakajima and Y. Sakamoto, Compact ECR ion source ... B37/38 (1989) 173
Tamura, M., see Horiuchi, M. ... B37/38 (1989) 285
Tamura, M., M. Horiuchi and Y. Kawamoto, Mask-size dependence of lattice defects generated by B- and As-implantation into submicron Si areas ... B37/38 (1989) 329
Tamura, S., see Tamura, Y. ... B37/38 (1989) 620
Tamura, S., M. Hyouzho, K. Yokota and S. Katayama, Growth of crystalline GaAs films on Si substrates by Ga and As ion beams ... B37/38 (1989) 862
Tamura, Y., M. Nogami, M. Tanaka, T. Maeda, H. Kumasaki and S. Tamura, Production implanter Nissin NH-20SR ... B37/38 (1989) 620
Tan Songsheng, see Xing Kunshan ... B37/38 (1989) 741
Tanabe, T., see Ikehata, T. ... B37/38 (1989) 107
Tanabe, T., see Mase, H. ... B37/38 (1989) 120
Tanaka, K., see Inami, H. ... B37/38 (1989) 198
Tanaka, M., see Sasaki, M. ... B37/38 (1989) 469
Tanaka, M., see Tamura, Y. ... B37/38 (1989) 620
Tanaka, M., see Usui, H. ... B37/38 (1989) 886
Tanaka, S., see Inoue, T. ... B37/38 (1989) 111
Tanaka, S., M. Akiba, M. Araki, S. Matsuda, Y. Matsuda, Y. Ohara, Y. Okumura, K. Yokoyama and K. Watanabe, Production of high current ion beams of various gas species from a magnetic multipole ion source ... B37/38 (1989) 128
Tanaka, S., see Tamba, M. ... B37/38 (1989) 173
Tanaka, S., see Tagami, T. ... B37/38 (1989) 256
Tanaka, S., see Arimatsu, K. ... B37/38 (1989) 833
Tanaka, S., see Hashimoto, I. ... B37/38 (1989) 838
Tanikawa, T., see Noguchi, T. ... B37/38 (1989) 632
Tanikawa, T., see Sunako, K. ... B37/38 (1989) 636

Tanizuka, N., Analysis of magnetron ion sources and PIG ion sources B37/38 (1989) 189
Ter Beek, J., see Polman, A. B37/38 (1989) 935
Thomae, R.W., H. Deitinghoff, J. Häuser, H. Klein, P. Leipe, A. Schempp, T. Weis, J. Bannenberg, W. Urbanus, R. Wojke and P.W. Van Amersfoort, Design study of high energy, high current rf accelerators for ion implantation B37/38 (1989) 235
Thomae, R.W., see Urbanus, W.H. B37/38 (1989) 508
Thompson, B., see Aihara, R. B37/38 (1989) 212
Thompson, G.R., see Kaufman, H.R. B37/38 (1989) 98
Thompson, G.R., see Stelmack, L.A. B37/38 (1989) 787
Thompson, M.O., see Poate, J.M. B37/38 (1989) 955
Thornton, R.P., R.G. Elliman and J.S. Williams, Epitaxial crystallisation of tin implanted silicon B37/38 (1989) 387
Thurman, C.T., see Stelmack, L.A. B37/38 (1989) 787
Ting, C.H., see Lin, H.-Y. B37/38 (1989) 960
Tokiguchi, K., see Amemiya, K. B37/38 (1989) 87
Tokiguchi, K., see Sakudo, N. B37/38 (1989) 184
Tokiguchi, K., K. Amemiya, H. Koike, T. Seki, N. Sakudo, S. Yamada and Y. Hirao, Ion beam acceleration using variable frequency RFQ B37/38 (1989) 253
Tokoro, N., see O'Connor, J.P. B37/38 (1989) 478
Tokuyama, T., Critical problems of ion implantation in processing small geometry integrated devices B37/38 (1989) 744
Tomita, K., see Uchitomi, N. B37/38 (1989) 810
Tonegawa, A., see Kogure, S. B37/38 (1989) 201
Torp, B., see Keller, R. B37/38 (1989) 74
Toyoda, N., see Uchitomi, N. B37/38 (1989) 810
Tsuboi, H., see Fukui, R. B37/38 (1989) 140
Tsuboi, H., see Takagi, K. B37/38 (1989) 169
Tsuboi, H., see Nishihashi, T. B37/38 (1989) 205
Tsuboi, H., see Mihara, Y. B37/38 (1989) 609
Tsuda, H., see Wada, M. B37/38 (1989) 132
Tsugueda, T., see Fukui, R. B37/38 (1989) 140
Tsugueda, T., see Takagi, K. B37/38 (1989) 169
Tsugueda, T., see Sunako, K. B37/38 (1989) 636
Tsuji, H., see Ishikawa, J. B37/38 (1989) 151
Tsuji, H., see Ishikawa, J. B37/38 (1989) 155
Tsuji, H., J. Ishikawa and T. Takagi, Slit extraction type compact microwave ion source B37/38 (1989) 159
Tsuji, H., J. Ishikawa, T. Maekawa and T. Takagi, Electron detachment cross-sections for heavy negative-ion beam B37/38 (1989) 231
Tsukakoshi, O., see Mihara, Y. B37/38 (1989) 609

Uchida, M., see Nunogaki, M. B37/38 (1989) 325
Uchitomi, N., H. Mikami, K. Tomita and N. Toyoda, Characterization of Si^+-implanted GaAs substrates using thermal-wave measurement B37/38 (1989) 810
Uchiyama, T., see Nishihashi, T. B37/38 (1989) 205
Uchiyama, T., see Mihara, Y. B37/38 (1989) 609
Ueda, N., see Nishihashi, T. B37/38 (1989) 205
Ueno, A., see Mori, Y. B37/38 (1989) 63
Ueno, T., see Ogawa, S. B37/38 (1989) 163
Umemura, K., Y. Kawanami and T. Ishitani, Development of an arsenic liquid-metal ion source B37/38 (1989) 208
Umemura, K., see Kawanami, Y. B37/38 (1989) 240
Urbanus, W., see Thomae, R.W. B37/38 (1989) 235
Urbanus, W.H., R.G.C. Wojke, J.G. Bannenberg, H. Klein, A. Schempp, R.W. Thomae, T. Weis and P.W. Van Amersfoort, MEQALAC: a 1-MeV multichannel rf-accelerator for light ions B37/38 (1989) 508
Urbanus, W.H., see Polman, A. B37/38 (1989) 935
Usami, M., see Yamaguchi, H. B37/38 (1989) 891
Usui, H., M. Tanaka, I. Yamada and T. Takagi, Size estimation of vaporized-metal clusters by electron microscope B37/38 (1989) 886

Valles, J.M., see White, A.E. B37/38 (1989) 923
Valvoda, V., see Musil, J. B37/38 (1989) 897
Van Amersfoort, P.W., see Thomae, R.W. B37/38 (1989) 235
Van Amersfoort, P.W., see Urbanus, W.H. B37/38 (1989) 508
Van Deenen, P.J., see Polman, A. B37/38 (1989) 935

Vanderpot, J.W., see Berrian, D.W. B37/38 (1989) 500
Vanderpot, J.W., see Berrian, D.W. B37/38 (1989) 518
Vantomme, A., see Langouche, G. B37/38 (1989) 438
Vasconcellos, M.A.Z., J.A.T. Borges da Costa, W.H. Schreiner and I.J.R. Baumvol, Surface metallurgy with high energy heavy ion beams B37/38 (1989) 653
Vredenberg, A.M., see Polman, A. B37/38 (1989) 935
Vyskočil, J., see Musil, J. B37/38 (1989) 897

Wada, M., H. Tsuda and M. Sasao, Production of negative lithium ions from the surface immersed in magnetic-field-free plasmas B37/38 (1989) 132
Wada, T. and A. Takeda, Electron-beam doping of Si into GaAs: the annealing behaviour of photoluminescence B37/38 (1989) 348
Wada, T. and A. Takeda, Electron beam doping of Si into GaAs in the overlayer Si/substrate GaAs and the sandwiched system of GaAs/Si/GaAs B37/38 (1989) 352
Wagner, A. and J.P. Levin, Focused ion beam repair of lithographic masks B37/38 (1989) 224
Wang Weiyuan, see Zhao Qihua B37/38 (1989) 336
Waszczak, J., see White, A.E. B37/38 (1989) 923
Watanabe, H., see Noguchi, T. B37/38 (1989) 632
Watanabe, H., see Sunako, K. B37/38 (1989) 636
Watanabe, K., see Inoue, T. B37/38 (1989) 111
Watanabe, K., see Tanaka, S. B37/38 (1989) 128
Watanabe, T., see Koyanagi, T. B37/38 (1989) 878
Wauk, M.T. and A.D. Giles, Performance of the Applied Materials PI9000 series ion implantation systems B37/38 (1989) 442
Wei, J., see Hiraki, A. B37/38 (1989) 799
Weis, T., see Thomae, R.W. B37/38 (1989) 235
Weis, T., see Urbanus, W.H. B37/38 (1989) 508
Weisenberger, W., S. Chereckdjian, P. Borden and W. Knodle, Real-time, in-situ particle monitoring in a high current ion implantation production bay B37/38 (1989) 644
Weschenfelder, F., see Meyer, O. B37/38 (1989) 917
Westendorp, J.F.M., R.E. Kaim, G.B. Odlum, R. Schreutelkamp, F.W. Saris and K.T.F. Janssen, Channeled implantation with a parallel scanned ion beam B37/38 (1989) 357
Westendorp, J.F.M., see Berrian, D.W. B37/38 (1989) 500
White, A.E., K.T. Short, J.P. Garno, J.M. Valles, R.C. Dynes, L.F. Schneemeyer, J. Waszczak, A.F.J. Levi, M. Anzlowar and K.W. Baldwin, Implantation, damage, and regrowth of high T_c superconductors B37/38 (1989) 923
White, N.R., Ion sources for use in ion implantation B37/38 (1989) 78
Wie, C.R., Effects of MeV ion bombardment and thermal annealing on $Ga_{1-x}In_xAs/GaAs$ B37/38 (1989) 965
Williams, J.M., R.A. Buchanan and I.-S. Lee, Ion beam processing of surgical materials B37/38 (1989) 676
Williams, J.S., see Thornton, R.P. B37/38 (1989) 387
Wittkower, A.B. and M.A. Guerra, SIMOX: buried layer formation by ion implantation – equipment and techniques B37/38 (1989) 512
Wojke, R., see Thomae, R.W. B37/38 (1989) 235
Wojke, R.G.C., see Urbanus, W.H. B37/38 (1989) 508
Wolf, G.K., M. Barth and W. Ensinger, Ion beam assisted deposition for metal finishing B37/38 (1989) 682
Wong, H., see Mutikainen, R.H. B37/38 (1989) 716
Wong, H., see Cheung, N.W. B37/38 (1989) 941
Wong, H., N.W. Cheung and S.S. Wong, Electronic defects in silicon induced by MeV carbon and oxygen implantations B37/38 (1989) 970
Wong, S.S., see Wong, H. B37/38 (1989) 970
Wu, M.F., see Langouche, G. B37/38 (1989) 438

Xi, X.X., see Meyer, O. B37/38 (1989) 917
Xia, W., M. Fernandes, C.A. Hewett, S.S. Lau, D.B. Poker and J.P. Biersack, On the temperature dependence and the moving species during ion mixing B37/38 (1989) 408
Xing Kunshan, Xu Xuemin, Chen Lizhi, Lin Chenglu, Tan Songsheng and Zou Shichang, An ion implanted SOM pressure sensor B37/38 (1989) 741
Xiong, G.C., see Meyer, O. B37/38 (1989) 917
Xu Xuemin, see Xing Kunshan B37/38 (1989) 741

Yabe, E., see Fukui, R. B37/38 (1989) 140
Yabe, E., see Shiono, T. B37/38 (1989) 166
Yamada, I., ICB deposition of almost perfect large single crystal Al films on silicon substrate B37/38 (1989) 770

Yamada, I., see Sosnowski, M. B37/38 (1989) 874
Yamada, I., see Usui, H. B37/38 (1989) 886
Yamada, I., see Yamamura, Y. B37/38 (1989) 902
Yamada, S., see Tokiguchi, K. B37/38 (1989) 253
Yamada, T., Y. Sato, H. Ogawa and T. Kimura, HIMAC PIG ion source development B37/38 (1989) 94
Yamaguchi, H., A. Shimase, S. Haraichi, M. Usami and T. Takahashi, Cutting of conductors on VLSI chips – a comparison between laser and focused ion beam removal B37/38 (1989) 891
Yamaguchi, K., see Tamba, M. B37/38 (1989) 173
Yamakawa, H., see Takagi, K. B37/38 (1989) 169
Yamakawa, H., see Nishihashi, T. B37/38 (1989) 205
Yamakawa, H., see Mihara, Y. B37/38 (1989) 609
Yamamura, Y., I. Yamada and T. Takagi, Computer studies of ionized cluster beam deposition B37/38 (1989) 902
Yamanaka, T., see Ohyu, K. B37/38 (1989) 749
Yamanishi, K., see Ina, T. B37/38 (1989) 779
Yamanishi, K., S. Yasunaga, Y. Kawagoe, K. Sato and K. Imada, Synthesis of superconducting Y–Ba–Cu–O thin films by ionized cluster beam codeposition B37/38 (1989) 930
Yamano, K., see Koyanagi, T. B37/38 (1989) 878
Yamashita, M., The effect of a magnetic field on the plasma characteristics of a sputter-type hf ion source B37/38 (1989) 194
Yamauchi, K., see Noguchi, T. B37/38 (1989) 632
Yamauchi, K., see Sunako, K. B37/38 (1989) 636
Yamawaki, M., see Tamba, M. B37/38 (1989) 173
Yang Genqing, Jiang Binyao, Zhou Wei, Liu Xianghuai and Zou Shichang, Dynamic implantation model of ion beam enhanced deposition B37/38 (1989) 424
Yarling, C.B. and W.A. Keenan, Ion implant rapid thermal anneal international round robin B37/38 (1989) 828
Yasunaga, S., see Yamanishi, K. B37/38 (1989) 930
Yokota, K., see Tamura, S. B37/38 (1989) 862
Yokota, Y., see Hiraki, A. B37/38 (1989) 799
Yokoyama, K., see Tanaka, S. B37/38 (1989) 128
Yoshida, M., see Ishikawa, K. B37/38 (1989) 317
Yoshida, Y., see Ohnishi, T. B37/38 (1989) 850
Yoshida, Y., T. Ohnishi, Y. Hirofuji, H. Iwasaki and T. Ikeda, Low-energy double ion-beam deposition of compound films B37/38 (1989) 866
Yoshitake, M., see Ogawa, S. B37/38 (1989) 163
Yoshitake, M., see Suzuki, Y. B37/38 (1989) 854
Yotsuya, T., see Suzuki, Y. B37/38 (1989) 854
Yugo, S., see Kimura, T. B37/38 (1989) 321

Zhang Hui, see Cheng Shichang B37/38 (1989) 136
Zhang, J.Z., see Chu, W.K. B37/38 (1989) 365
Zhang, M., see Pan, X. B37/38 (1989) 858
Zhao Qihua, Jiang Xinyuan, Lin Chenglu, Fan Weidong, Wang Weiyuan and Liu Xianghuai, SiF_n-implanted GaAs and shallow junctions B37/38 (1989) 336
Zhou Wei, see Lin Chenglu B37/38 (1989) 384
Zhou Wei, see Yang Genqing B37/38 (1989) 424
Zhu, Z., see Pan, X. B37/38 (1989) 858
Zou Shichang, see Lin Chenglu B37/38 (1989) 384
Zou Shichang, see Yang Genqing B37/38 (1989) 424
Zou Shichang and Liu Xianghuai, Ion implantation in China B37/38 (1989) 672
Zou Shichang, see Xing Kunshan B37/38 (1989) 741
Zrudsky, D.R. and R.B. Simonton, Sheet resistance uniformity monitoring of a medium-current ion implanter . B37/38 (1989) 361
Zuhr, R.A., S.J. Pennycook, T.S. Noggle, N. Herbots, T.E. Haynes and B.R. Appleton, Ion beam deposition in materials research B37/38 (1989) 16